



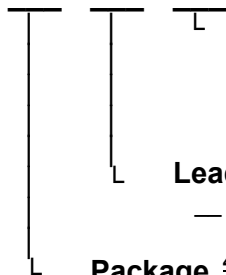
Solid State Devices, Inc.

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DESIGNER'S DATA SHEET

Part Number / Ordering Information ^{1/}

SFF100N20



Screening ^{2/}

— = Not Screened
TX = TX Level
TXV = TXV Level
S = S Level

Lead Option

— = Straight Leads

Package ^{4/}

/3T= TO-3 (Pin Diameter : 0.058"-0.063")

SFF100N20/3T

**100 AMP , 200 Volts, 25 mΩ
Avalanche Rated N-channel
MOSFET**

Features:

- Rugged poly-Si gate
- Lowest ON-resistance in the industry
- Avalanche rated
- Hermetically Sealed, Power Package with high pin current carrying capability
- Low Total Gate Charge
- Fast Switching
- TX, TXV, S-Level screening available
- Improved ($R_{DS(ON)}$ Q_G) figure of merit

Maximum Ratings ^{5/}		Symbol	Value	Units
Drain - Source Voltage		V_{DSS}	200	V
Gate – Source Voltage	continuous	V_{GS}	±20	V
	transient		±30	
Max. Continuous Drain Current (package limited)	@ $T_C = 25^\circ C$	I_{D1}	55	A
Max. Instantaneous Drain Current (T_J limited)	@ $T_C = 25^\circ C$	I_{D2}	100	A
	@ $T_C = 125^\circ C$	I_{D3}	40	
Max. Avalanche current	@ $L = 0.1$ mH	I_{AR}	60	A
Single and Repetitive Avalanche Energy	@ $L = 0.1$ mH	E_{AS}	1500	mJ
		E_{AR}	50	
Total Power Dissipation	@ $T_C = 25^\circ C$	P_D	300	W
Operating & Storage Temperature		T_{OP} & T_{STG}	-55 to +175	$^\circ C$
Maximum Thermal Resistance (Junction to Case)		$R_{\theta JC}$	0.5 (typ.0.3)	$^\circ C/W$

NOTES:

*Pulse Test: Pulse Width = 300μsec, Duty Cycle = 2%.

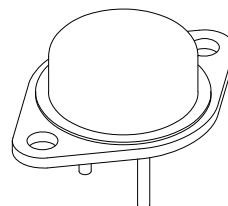
^{1/} For ordering information, price, and availability - contact factory.

^{2/} Screening based on MIL-PRF-19500. Screening flows available on request.

^{4/} Maximum current limited by package configuration

^{5/} Unless otherwise specified, all electrical characteristics @25 $^\circ C$.

TO-3



NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

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SFF100N20/3T

Electrical Characteristics ^{5/}		Symbol	Min	Typ	Max	Units
Drain to Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	200	220	—	V
Drain to Source On State Resistance	$V_{GS} = 10V, I_D = 48A, T_j = 25^\circ C$	$R_{DS(on)}$	—	25	30	mΩ
	$V_{GS} = 10V, I_D = 48A, T_j = 125^\circ C$		—	50	65	
	$V_{GS} = 10V, I_D = 48A, T_j = 175^\circ C$		—	65	—	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 4.0mA, T_j = 25^\circ C$	$V_{GS(th)}$	2.5	4.5	5.0	V
	$V_{DS} = V_{GS}, I_D = 4.0mA, T_j = 125^\circ C$		1.5	3.6	—	
	$V_{DS} = V_{GS}, I_D = 4.0mA, T_j = -55^\circ C$		—	5	6	
Gate to Source Leakage	$V_{GS} = \pm 20V, T_j = 25^\circ C$	I_{GSS}	—	10	±100	nA
	$V_{GS} = \pm 20V, T_j = 125^\circ C$		—	30	—	
Zero Gate Voltage Drain Current	$V_{DS} = 200V, V_{GS} = 0V, T_j = 25^\circ C$	I_{DSS}	—	0.01	25	μA
	$V_{DS} = 200V, V_{GS} = 0V, T_j = 125^\circ C$		—	2.5	150	μA
	$V_{DS} = 200V, V_{GS} = 0V, T_j = 150^\circ C$		—	25	—	μA
Forward Transconductance	$V_{DS} = 10V, I_D = 48A, T_j = 25^\circ C$	g_{fs}	25	50	—	Mho
Total Gate Charge	$V_{GS} = 10V$	Q_g	—	150	250	nC
Gate to Source Charge	$V_{DS} = 100V$	Q_{gs}	—	45	65	
Gate to Drain Charge	$I_D = 48A$	Q_{gd}	—	75	120	
Turn on Delay Time	$V_{GS} = 10V$	$t_{d(on)}$	—	50	75	nsec
Rise Time	$V_{DS} = 100V$	t_r	—	50	75	
Turn off Delay Time	$I_D = 48A$	$t_{d(off)}$	—	110	135	
Fall Time	$R_G = 4.0\Omega, pw = 3\mu s$	t_f	—	50	75	
Diode Forward Voltage	$I_F = 48A, V_{GS} = 0V$	V_{SD}	—	0.90	1.5	V
Diode Reverse Recovery Time Reverse Recovery Charge	$I_F = 10A, di/dt = 100A/\mu sec$	t_{rr1}	—	190	250	nsec
	$I_F = 10A, di/dt = 100A/\mu sec$	I_{rm1}	—	11	—	A
	$I_F = 10A, di/dt = 100A/\mu sec$	Q_{rr1}	—	1	—	μC
	$I_F = 25A, di/dt = 100A/\mu sec$	t_{rr2}	—	310	—	nsec
	$I_F = 25A, di/dt = 100A/\mu sec$	I_{rm2}	—	17	—	A
	$I_F = 25A, di/dt = 100A/\mu sec$	Q_{rr2}	—	2.5	—	μC
Input Capacitance	$V_{GS} = 0V$	C_{iss}	—	5300	—	pF
Output Capacitance	$V_{DS} = 25V$	C_{oss}	—	1050	—	
Reverse Transfer Capacitance	$f = 1 MHz$	C_{rss}	—	175	—	

Package Outline: TO-3

Pin Out:

Pin 1: GATE

Pin 2: SOURCE

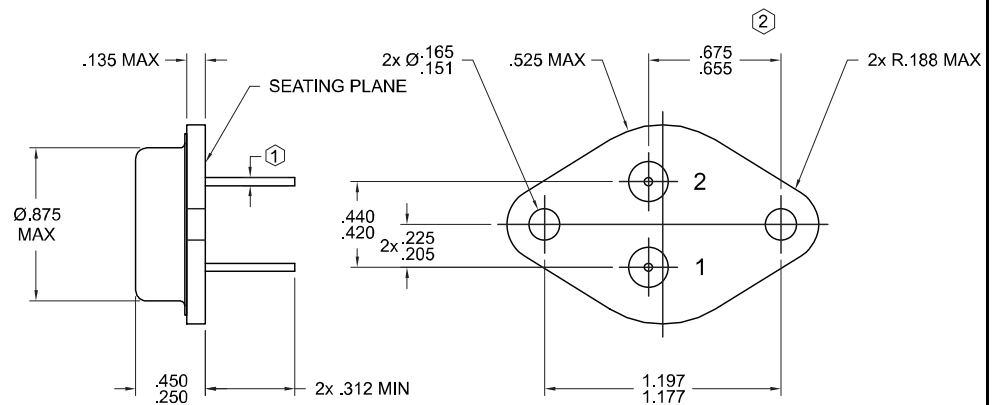
Pin 3: DRAIN

Note 1:

P/N: SFF80N20/3T:
Pin Diameter: 0.063"
0.058"

Note 2:

This dimension shall be measured at points .050 - .055" below the seating plane. When gage is not used, measurement will be made at seating plane. This outline does not meet the minimum criteria established by JS-10 for registration.



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